

## MOSFET Silicon N-Channel MOS



### 1. Applications

Single-ended flyback or two-transistor forward topologies.  
PC power, PD Adaptor, LCD & PDP TV and LED lighting.

### 2. Features

Low drain-source on-resistance:  $R_{DS(ON)} = 620\text{m}\Omega$  (typ.)  
Easy to control Gate switching  
Enhancement mode:  $V_{th} = 2.8$  to  $4.2\text{ V}$

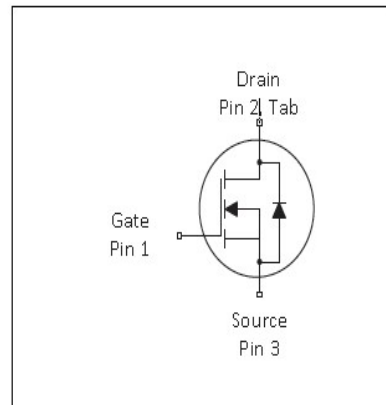


**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	850	V
$R_{DS(on),max}$	710	$\text{m}\Omega$
$Q_{g,typ}$	18.5	nC
$I_{D,pulse}$	35	A

### 3. Packaging and Internal Circuit

Part Name	Package	Marking
ASA80R900E	TO220F	ASA80R900E



## 1 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$		-	8.5	A	$T_C=25^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	35	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	88	mJ	$T_C=25^\circ\text{C}$ , $V_{DD}=50\text{V}$ , $I_{av}=4.2\text{A}$ , $L=10\text{mH}$ , $R_G=25\Omega$
Avalanche current, single pulse	$I_{AR}$	-	-	4.2	A	$T_C=25^\circ\text{C}$ , $V_{DD}=50\text{V}$ , $L=10\text{mH}$ , $R_G=25\Omega$
Gate source voltage (static)	$V_{GS}$	-30	-	30	V	static;
Power dissipation	$P_{tot}$	-	-	43	W	$T_C=25^\circ\text{C}$
Storage temperature	$T_{stg}$	-55	-	150	$^\circ\text{C}$	
Operating junction temperature	$T_j$	-55	-	150	$^\circ\text{C}$	

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum Duty Cycle  $D = 0.50$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_G$

## 2 Thermal characteristics

### Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	3.26	°C/W	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	76	°C/W	device on PCB, minimal footprint

### 3 Electrical characteristics

at  $T_j=25^{\circ}\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	800	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{(GS)th}$	2.8		4.2	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=800V, V_{GS}=0V, T_j=25^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=30V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	620	710	m $\Omega$	$V_{GS}=10V, I_D=6A, T_j=25^{\circ}\text{C}$
Gate resistance (Intrinsic)	$R_G$	-	25	-	$\Omega$	$f=1\text{MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	850.8	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Output capacitance	$C_{oss}$	-	34.4	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Reverse transfer capacitance	$C_{rss}$	-	0.92	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	-	40.6	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Rise time	$t_r$	-	34.8	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Turn-off delay time	$t_{d(off)}$	-	128	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Fall time	$t_f$	-	31	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$

**Table 6 Gate charge characteristics**

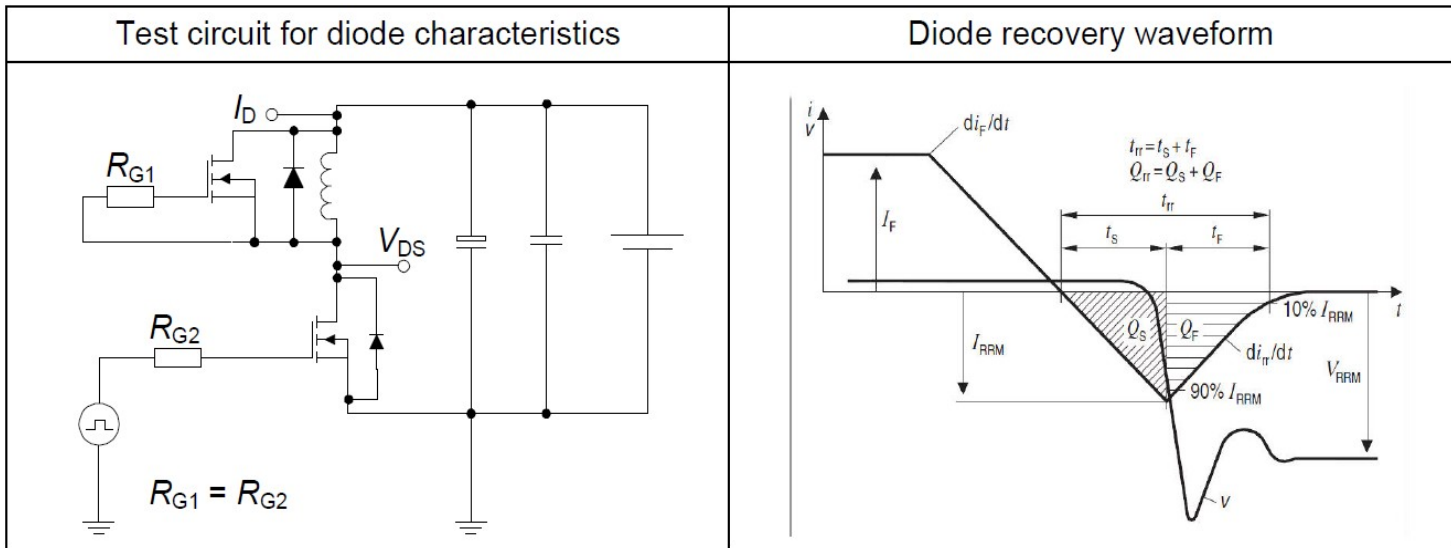
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	5.0	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V
Gate to drain charge	$Q_{gd}$	-	6.6	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V
Gate charge total	$Q_g$	-	18.5	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V

**Table 7 Reverse diode characteristics**

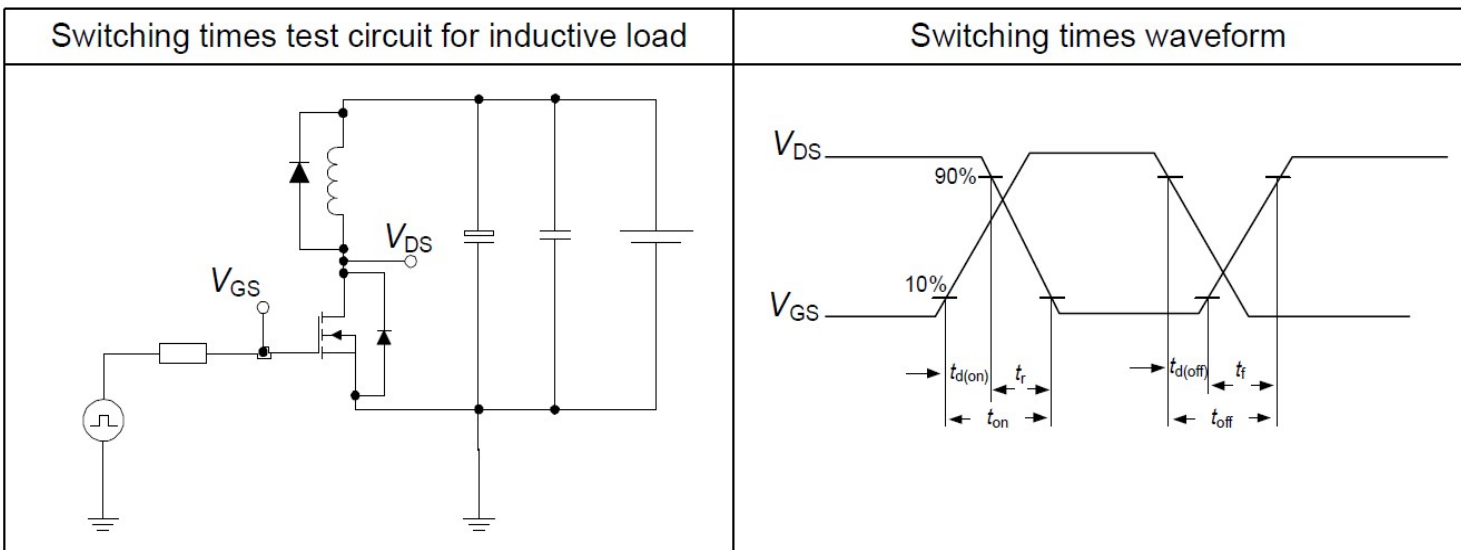
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.75	-	V	$V_{GS}=0V, I_F=1A, T_j=25^{\circ}C$
Reverse recovery time	$t_{rr}$	-	266.5	-	ns	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$
Reverse recovery charge	$Q_{rr}$	-	2.2	-	uC	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$
Peak reverse recovery current	$I_{rrm}$	-	14	-	A	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$

## 4 Test Circuits

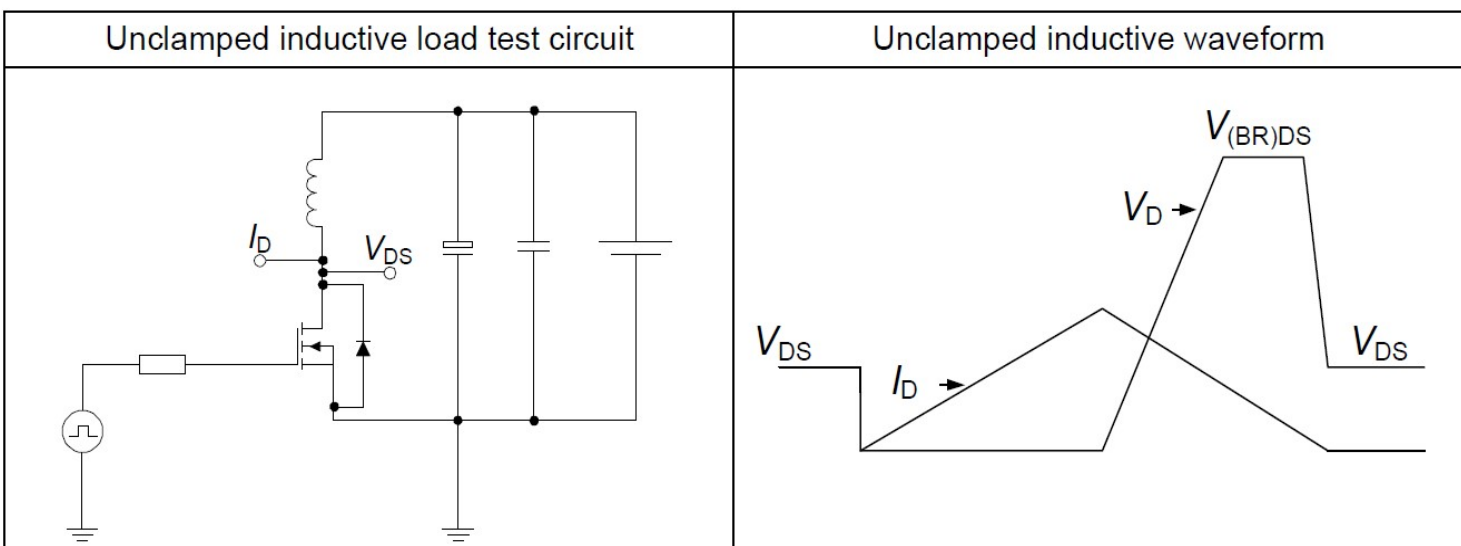
**Table 8 Diode characteristics**



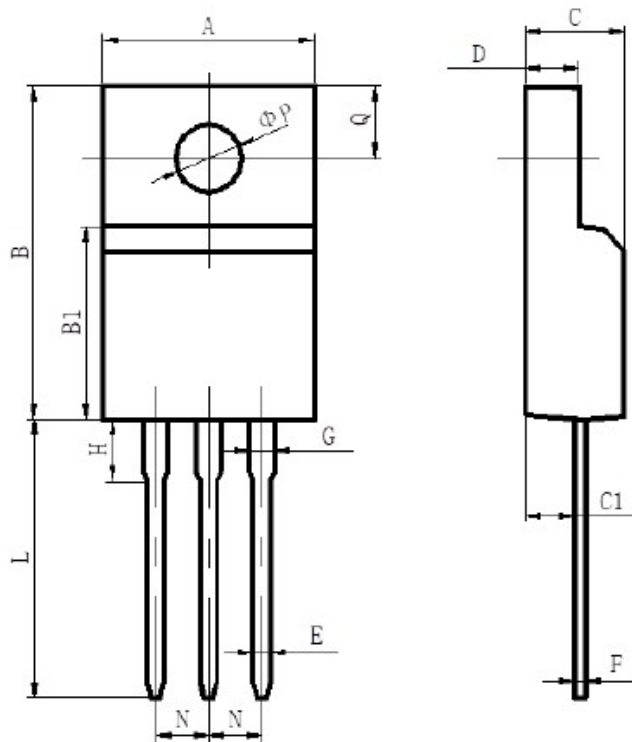
**Table 9 Switching times**



**Table 10 Unclamped inductive load**



### 5 Package Outlines



項目	規範(mm)	
	MIN	MAX
A	9.70	10.30
B	15.50	16.10
B1	8.99	9.39
C	4.40	4.80
C1	2.15	2.55
D	2.50	2.90
E	0.70	0.90
F	0.40	0.60
G	1.12	1.42
H	3.40	3.80
L	12.6	13.6
N	2.34	2.74
Q	3.15	3.55
$\phi P$	3.00	3.30

Outline PG-TO220F

## Revision History

Revision	Date	Subjects (major changes since last revision)
1.0	2021-11-4	Preliminary version